Abstracts

A Monolithic GaAs I.F. Amplifier for Integrated Receiver Applications

---

D.R. Decker, A.K. Gupta, W. Petersen and D.R. Ch'en. "A Monolithic GaAs I.F. Amplifier for Integrated Receiver Applications." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 363-366.

A monolithic GaAs integrated amplifier has been constructed for the 500 to 1000 MHz intermediate frequency band. The amplifier provides 8.0 ± 1.5 dB gain across the band. The output of the amplifier utilizes a source follower configuration to obtain a favorably low output VSWR of less than 1.5:1 (return loss >15 dB). All bias lines with integral bypass capacitors are contained on the chip and this amplifier is suitable for further integration as a building block of a monolithically integrated receiver front end.

❑ Return to main document.

Click on title for a complete paper.